

March 1994 Revised November 1999

74ABT2240

Octal Buffer/Line Driver with 25 Ω Series Resistors in the Outputs

General Description

The ABT2240 is an inverting octal buffer and line driver designed to drive the capacitive inputs of MOS memory drivers, address drivers, clock drivers, and bus-oriented

The 25Ω series resistors in the outputs reduce ringing and eliminate the need for external resistors.

Features

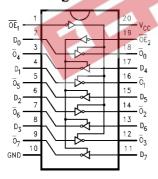
- Guaranteed latchup protection
- lacktriangle High impedance glitch-free bus loading during entire power up and power down cycle
- Nondestructive hot insertion capability

Ordering Code:

		38 (33)
Order Number	Package Number	Package Description
74ABT2240CSC	M20B	20-Lead Small Outline Integrated Circuit (SOIC), JEDEC MS-013, 0.300" Wide Body
74ABT2240CSJ	M20D	20-Lead Small Outline Package (SOP), EIAJ TYPE II, 5.3mm Wide
74ABT2240CMSA	MSA20	20-Lead Shrink Small Outline Package (SSOP), EIAJ TYPE II, 5.3mm Wide
74ABT2240CMTC	MTC20	20-Lead Thin Shrink Small Outline Package (TSSOP), JEDEC MO-153, 4.4mm Wide

Devices also available in Tape and Reel. Specify by appending letter suffix "X" to the ordering code.

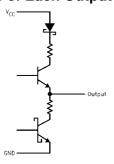
Connection Diagram



Pin Descriptions

Pin Names	Descriptions				
$\overline{OE}_1, \overline{OE}_2$	Output Enable Input (Active LOW)				
D ₀ -D ₇	Data Inputs				
$\overline{O}_0 - \overline{O}_7$	Outputs				

Schematic of Each Output



Truth Table

OE ₁	I ₀₋₃	Ō ₀₋₃	OE ₂	I ₄₋₇	Ō ₄₋₇
Н	Х	Z	Н	Х	Z
L	Н	L	L	Н	L
L	L	Н	L	L	Н

- H = HIGH Voltage Level
- L = LOW Voltage Level X = Immaterial
- Z = High Impedance

Absolute Maximum Ratings(Note 1)

Recommended Operating Conditions

 $\begin{array}{ll} \mbox{Storage Temperature} & -65\mbox{°C to } +150\mbox{°C} \\ \mbox{Ambient Temperature under Bias} & -55\mbox{°C to } +125\mbox{°C} \\ \end{array}$

 $\begin{tabular}{lll} Ambient Temperature under Bias & -55^{\circ}C to +125^{\circ}C \\ Junction Temperature under Bias & -55^{\circ}C to +150^{\circ}C \\ \end{tabular}$

 $\begin{array}{lll} \text{V}_{\text{CC}} \text{ Pin Potential to Ground Pin} & -0.5 \text{V to } +7.0 \text{V} \\ \text{Input Voltage (Note 2)} & -0.5 \text{V to } +7.0 \text{V} \\ \text{Input Current (Note 2)} & -30 \text{ mA to } +5.0 \text{ mA} \\ \end{array}$

Voltage Applied to Any Output

in the Disabled or

 $\begin{array}{ll} \mbox{Power-off State} & -0.5\mbox{V to } 5.5\mbox{V} \\ \mbox{in the HIGH State} & -0.5\mbox{V to } \mbox{V}_{\mbox{CC}} \end{array}$

Current Applied to Output

in LOW State (Max) twice the rated I_{OL} (mA)

DC Latchup Source Current

(Across Comm Operating Range) -300 mA Over Voltage Latchup (I/O) 10V Free Air Ambient Temperature -40°C to $+85^{\circ}\text{C}$ Supply Voltage +4.5V to +5.5V

Minimum Input Edge Rate (ΔV/Δt)

Data Input 50 mV/ns
Enable Input 20 mV/ns

Note 1: Absolute maximum ratings are values beyond which the device may be damaged or have its useful life impaired. Functional operation under these conditions is not implied.

Note 2: Either voltage limit or current limit is sufficient to protect inputs.

DC Electrical Characteristics

Vih	Symbol	Parar	neter	Min	Тур	Max	Units	V _{CC}	Conditions
V _{CD} Input Clamp Diode Voltage −1.2 V Min I _{IN} =−18 mA V _{OH} Output HIGH 2.5 V Min I _{OH} =−3 mA V _{OL} Output LOW Voltage 0.8 V Min I _{OH} =−32 mA I _{IH} Input HIGH Current 1 µA Max V _{IN} = 2.7V (Note 3) V _{IN} = V _{CC} 1 µA Max V _{IN} = 2.7V (Note 3) V _{IN} = V _{CC} 1 µA Max V _{IN} = 7.0V I _{IL} Input LOW Current −1 µA Max V _{IN} = 0.5V (Note 3) V _{IN} = 0.5V (Note 3) V _{IN} = 0.5V (Note 3) V _{IN} = 0.5V (Note 3) V _{IN} = 0.0V V _{ID} Input Leakage Test V 0.0 I _{ID} = 1.9 µA All Other Pins Grounded I _{OZH} V _{IN} = 0.5V (Note 3) V _{IN} = 0.5V (Note 3) I _{OZH} Output Leakage Current 10 µA 0 − 5.5V (Note 3) V _{IN} = 2.7V; OE n = 2.0V I _{OZH} Output Leakage Current 10 µA 0 − 5.5V (Note 3) N _{ID} = 1.9 µA <t< td=""><td>V_{IH}</td><td>Input HIGH Voltage</td><td></td><td>2.0</td><td>26</td><td>43</td><td>V</td><td>100</td><td>Recognized HIGH Signal</td></t<>	V _{IH}	Input HIGH Voltage		2.0	26	43	V	100	Recognized HIGH Signal
Voh	V _{IL}	Input LOW Voltage			130	0.8	V		Recognized LOW Signal
Voltage Vol	V _{CD}	Input Clamp Diode Vo	ltage			-1.2	V	Min	I _{IN} = -18 mA
Vol. Output LOW Voltage 0.8 V Min I _{OL} = 15 mA	V _{OH}	Output HIGH		2.5	,		V	Min	$I_{OH} = -3 \text{ mA}$
Input HIGH Current 1		Voltage		2.0			V	Min	$I_{OH} = -32 \text{ mA}$
Input HIGH Current Breakdown Test 7	V _{OL}	Output LOW Voltage				8.0	V	Min	I _{OL} = 15 mA
I _{BVI} Input HIGH Current Breakdown Test 7	I _{IH}	Input HIGH Current				1	Δ	May	V _{IN} = 2.7V (Note 3)
Input LOW Current						1	μΑ	IVIAX	$V_{IN} = V_{CC}$
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	I _{BVI}	Input HIGH Current Bi	reakdown Test			7	μΑ	Max	V _{IN} = 7.0V
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	I _{IL}	Input LOW Current				-1		Max	V _{IN} = 0.5V (Note 3)
All Other Pins Grounded I_{OZH} Output Leakage Current 10 μA 0 - 5.5V $V_{OUT} = 2.7V$; $\overline{OEn} = 2.0V$ I_{OZL} Output Leakage Current -10 μA 0 - 5.5V $V_{OUT} = 0.5V$; $\overline{OEn} = 2.0V$ I_{OS} Output Short-Circuit Current -275 mA Max $V_{OUT} = 0.0V$ I_{CEX} Output HIGH Leakage Current 50 μA Max $V_{OUT} = V_{CC}$ I_{ZZ} Bus Drainage Test 100 μA 0.0 $V_{OUT} = 5.5V$; All Others GND I_{CCH} Power Supply Current 50 μA Max All Outputs HIGH I_{CCL} Power Supply Current 50 μA Max All Outputs LOW I_{CCZ} Power Supply Current 50 μA Max $\overline{OEn} = V_{CC}$ All Others at V_{CC} or GND						-1	μΛ	IVIAX	$V_{IN} = 0.0V$
I_{OZH} Output Leakage Current 10 μA 0 - 5.5V $V_{OUT} = 2.7V$; $\overline{OEn} = 2.0V$ I_{OZL} Output Leakage Current -10 μA 0 - 5.5V $V_{OUT} = 0.5V$; $\overline{OEn} = 2.0V$ I_{OS} Output Short-Circuit Current -275 mA Max $V_{OUT} = 0.0V$ I_{CEX} Output HIGH Leakage Current 50 μA Max $V_{OUT} = V_{CE}$ I_{ZZ} Bus Drainage Test 100 μA 0.0 $V_{OUT} = 5.5V$; All Others GND I_{CCH} Power Supply Current 50 μA Max All Outputs HIGH I_{CCL} Power Supply Current 30 mA Max All Outputs LOW I_{CCZ} Power Supply Current 50 μA Max $\overline{OEn} = V_{CC}$ All Others at V_{CC} or GND	V _{ID}	Input Leakage Test					V	0.0	$I_{ID} = 1.9 \mu A$
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$									All Other Pins Grounded
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	l _{OZH}	Output Leakage Curre	ent			10	μΑ	0 – 5.5V	V _{OUT} = 2.7V; OE n = 2.0V
	l _{OZL}	Output Leakage Curre	ent			-10	μΑ	0 – 5.5V	V _{OUT} = 0.5V; OE n = 2.0V
$\begin{tabular}{ c c c c c c c c c c c c c c c c c c c$	los	'				-275	mA	Max	V _{OUT} = 0.0V
I _{CCH} Power Supply Current 50 μA Max All Outputs HIGH I _{CCL} Power Supply Current 30 mA Max All Outputs LOW I _{CCZ} Power Supply Current 50 μA Max $\overline{\text{OEn}} = \text{V}_{CC}$ All Others at V _{CC} or GND	I _{CEX}	Output HIGH Leakage	Current			50	μΑ	Max	V _{OUT} = V _{CC}
$\begin{tabular}{ c c c c c c c c c c c c c c c c c c c$	I_{ZZ}	Bus Drainage Test				100	μΑ	0.0	V _{OUT} = 5.5V; All Others GND
I_{CCZ} Power Supply Current 50 μA $\overline{OEn} = V_{CC}$ All Others at V_{CC} or GND	I _{CCH}	Power Supply Current				50	μΑ	Max	All Outputs HIGH
All Others at V _{CC} or GND	I _{CCL}	Power Supply Current				30	mA	Max	All Outputs LOW
	I _{CCZ}	Power Supply Current				50	μΑ	Max	OEn = V _{CC}
Additional Outside England 4.5 mg V V 2.4V									All Others at V _{CC} or GND
ICCT Additional Outputs Enabled 1.5 mA V _I = V _{CC} - 2.1V	I _{CCT}	Additional	Outputs Enabled			1.5	mA		$V_I = V_{CC} - 2.1V$
I_{CC} /Input Outputs 3-STATE 1.5 mA Max Enable Input $V_1 = V_{CC} - 2.1V$		I _{CC} /Input	Outputs 3-STATE			1.5	mA	Max	Enable Input V _I = V _{CC} - 2.1V
Outputs 3-STATE 50 μA Data Input $V_I = V_{CC} - 2.1 V$			Outputs 3-STATE			50	μΑ		Data Input V _I = V _{CC} - 2.1V
All Others at V _{CC} or GND									All Others at V _{CC} or GND
I _{CCD} Dynamic I _{CC} No Load mA/ Outputs OPEN	I _{CCD}	Dynamic I _{CC}	No Load				mA/		Outputs OPEN
(Note 3) 0.1 MHz Max OEn = GND (Note 4)		(Note 3)				0.1	MHz	Max	OEn = GND (Note 4)
One Bit Toggling, 50% Duty Cy									One Bit Toggling, 50% Duty Cycle

Note 3: Guaranteed, but not tested.

Note 4: For 8 bits toggling, $I_{CCD} < 0.8 \ \text{mA/MHz}.$

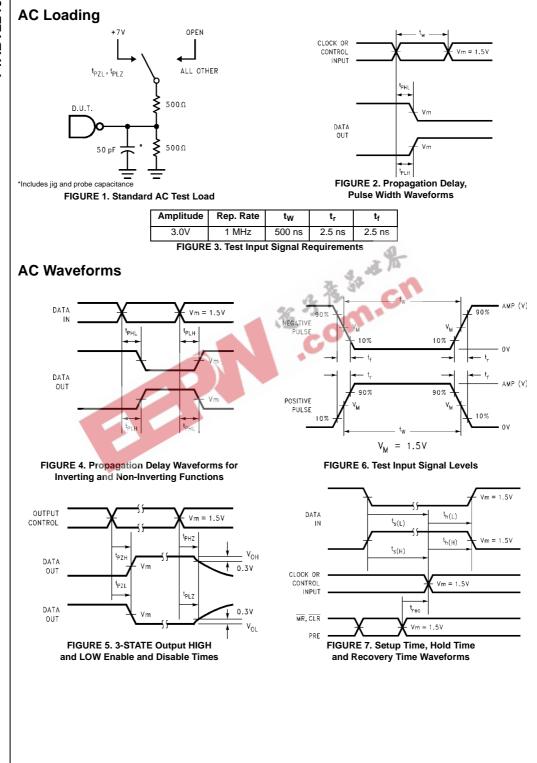
AC Electrical Characteristics

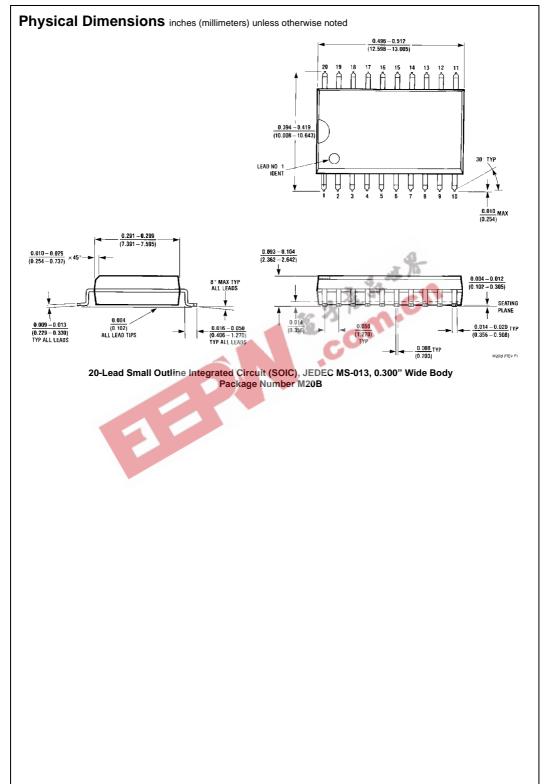
Symbol	Parameter		$T_A = +25$ °C $V_{CC} = +5V$ $C_1 = 50 \text{ pF}$			$T_A = -40^{\circ}\text{C to } +85^{\circ}\text{C}$ $V_{CC} = 4.5\text{V} - 5.5\text{V}$ $C_L = 50 \text{ pF}$	
		Min	Тур	Max	Min	Max	
t _{PLH}	Propagation	1.0		4.9	1.0	4.9	
t _{PHL}	Delay Data to Outputs	1.5		5.3	1.5	5.3	ns
t _{PZH}	Output Enable	1.5		6.6	1.5	6.6	
t _{PZL}	Time	2.7		6.9	2.7	6.9	ns
t _{PHZ}	Output Disable	1.9		6.4	1.9	6.4	
t _{PLZ}	Time	1.9		6.4	1.9	6.4	ns

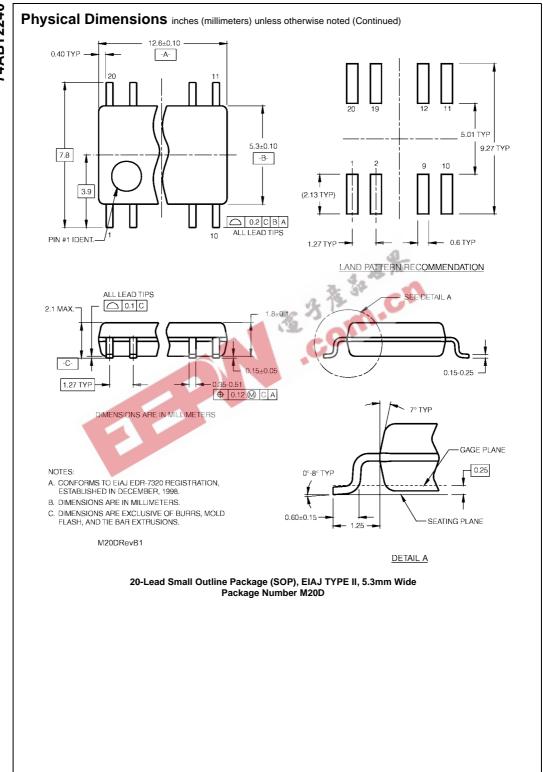
Capacitance

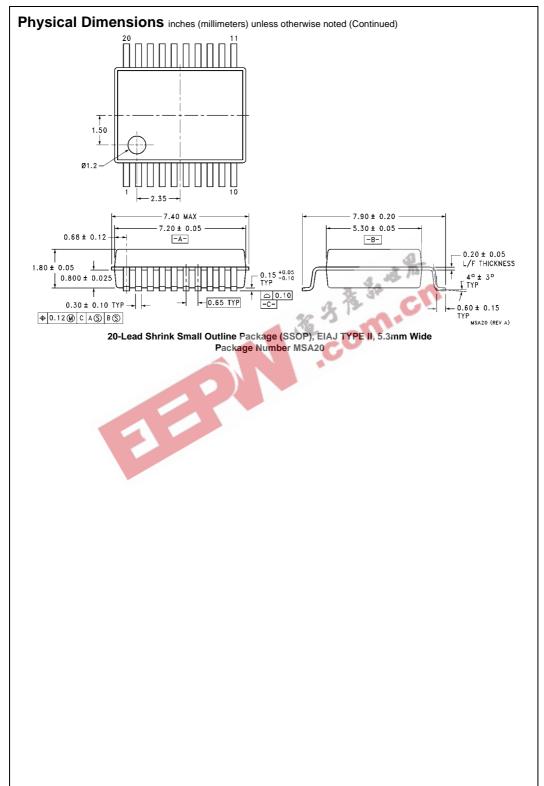
Symbol	Parameter	Тур	Units	Conditions T _A = 25°C
C _{IN}	Input Capacitance	5.0	pF	V _{CC} = 0V
C _{OUT} (Note 5)	Output Capacitance	9.0	pF	V _{CC} = 5.0V
	pasured at frequency f = 1 MHz, per MIL-STD-		CON	n.cn

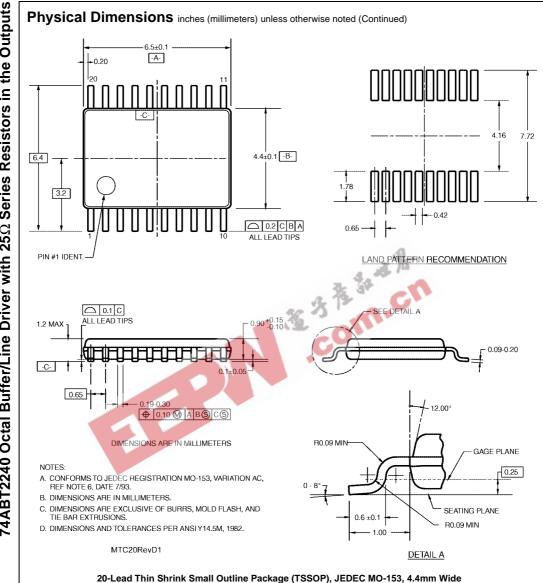












Package Number MTC20

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- 2. A critical component in any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

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